

**15A, 1000V Ultrafast Dual Diode**

The RURH15100CC is an ultrafast dual diode with soft recovery characteristics ( $t_{rr} < 100\text{ns}$ ). It has low forward voltage drop and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheel/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits, reducing power loss in the switching transistors.

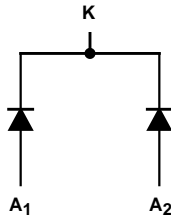
Formerly developmental type TA09906.

**Ordering Information**

PART NUMBER	PACKAGE	BRAND
RURH15100CC	TO-218AC	URH15100C

NOTE: When ordering, use the entire part number.

**Symbol**



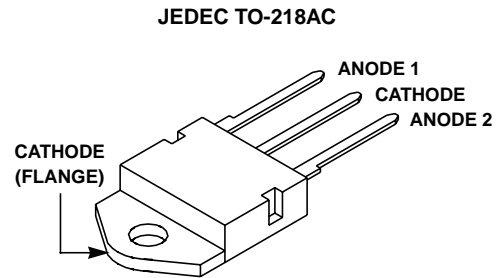
**Features**

- Ultrafast with Soft Recovery . . . . . <100ns
- Operating Temperature . . . . . 175°C
- Reverse Voltage . . . . . 1000V
- Avalanche Energy Rated
- Planar Construction

**Applications**

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

**Packaging**



**Absolute Maximum Ratings** (Per Leg)  $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

	RURH15100CC	UNITS
Peak Repetitive Reverse Voltage . . . . . $V_{RRM}$	1000	V
Working Peak Reverse Voltage . . . . . $V_{RWM}$	1000	V
DC Blocking Voltage . . . . . $V_R$	1000	V
Average Rectified Forward Current . . . . . $I_{F(AV)}$ ( $T_C = 142^\circ\text{C}$ )	15	A
Repetitive Peak Surge Current . . . . . $I_{FRM}$ (Square Wave 20kHz)	30	A
Nonrepetitive Peak Surge Current . . . . . $I_{FSM}$ (Halfwave, 1 Phase 60Hz)	200	A
Maximum Power Dissipation . . . . . $P_D$	100	W
Avalanche Energy (See Figures 7 and 8) . . . . . $E_{AVL}$	20	mJ
Operating and Storage Temperature . . . . . $T_{STG}, T_J$	-65 to 175	°C

**Electrical Specifications** (Per Leg)  $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	
$V_F$	$I_F = 15\text{A}$	-	-	1.8	V
	$I_F = 15\text{A}, T_C = 150^\circ\text{C}$	-	-	1.5	V
$I_R$	$V_R = 1000\text{V}$	-	-	100	$\mu\text{A}$
	$V_R = 1000\text{V}, T_C = 150^\circ\text{C}$	-	-	500	$\mu\text{A}$
$t_{rr}$	$I_F = 1\text{A}, t \text{ d}I_F/\text{d}t = 100\text{A}/\mu\text{s}$	-	-	100	ns
	$I_F = 15\text{A}, t \text{ d}I_F/\text{d}t = 100\text{A}/\mu\text{s}$	-	-	125	ns
$t_a$	$I_F = 15\text{A}, t \text{ d}I_F/\text{d}t = 100\text{A}/\mu\text{s}$	-	75	-	ns
$t_b$	$I_F = 15\text{A}, t \text{ d}I_F/\text{d}t = 100\text{A}/\mu\text{s}$	-	40	-	ns
$R_{\theta\text{JC}}$		-	-	1.5	$^\circ\text{C}/\text{W}$

**DEFINITIONS**

$V_F$  = Instantaneous forward voltage ( $p_w = 300\mu\text{s}$ ,  $D = 2\%$ ).

$I_R$  = Instantaneous reverse current.

$t_{rr}$  = Reverse recovery time at  $dI_F/dt = 100\text{A}/\mu\text{s}$  (See Figure 6), summation of  $t_a + t_b$ .

$t_a$  = Time to reach peak reverse current at  $dI_F/dt = 100\text{A}/\mu\text{s}$  (See Figure 6).

$t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 6).

$R_{\theta\text{JC}}$  = Thermal resistance junction to case.

$p_w$  = Pulse width.

$D$  = Duty cycle.

**Typical Performance Curves**

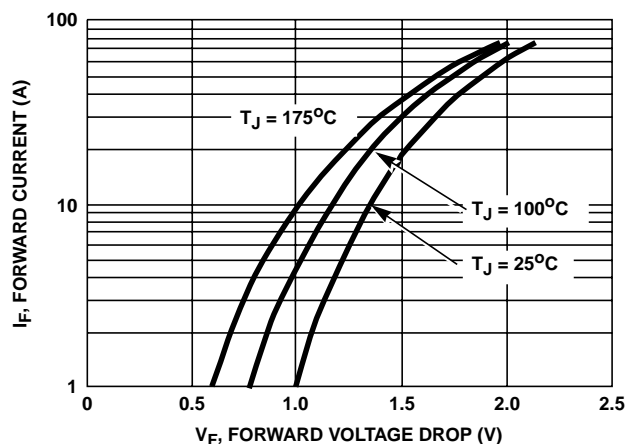


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

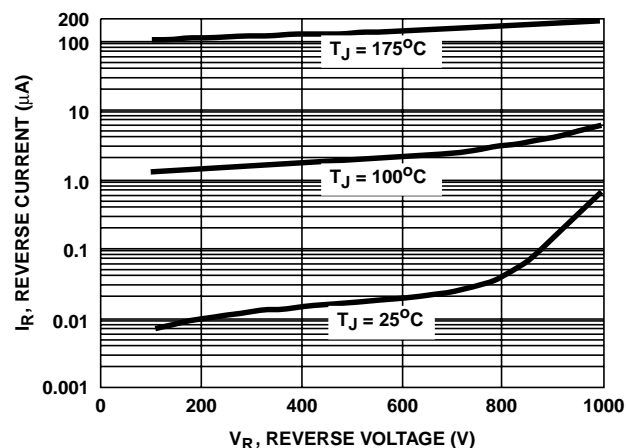


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

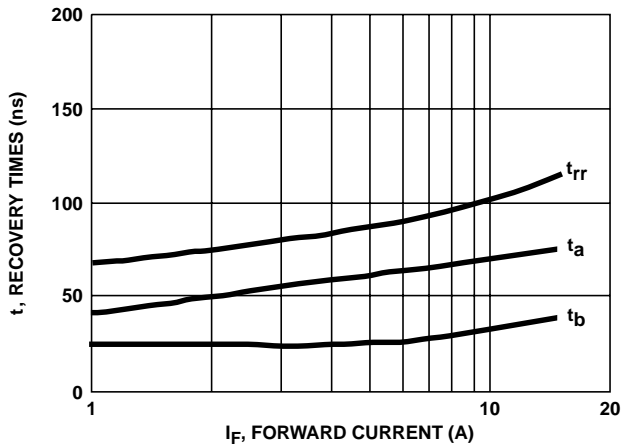


FIGURE 3.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

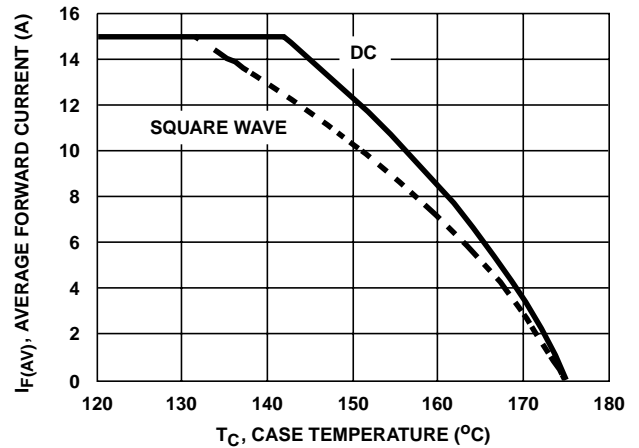


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

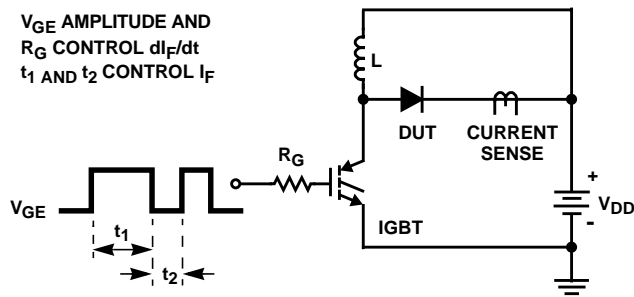


FIGURE 5.  $t_{rr}$  TEST CIRCUIT

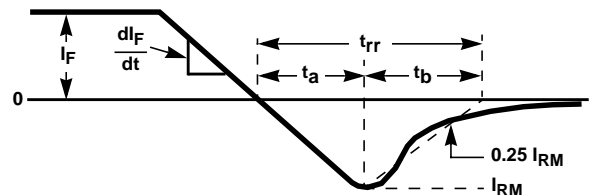


FIGURE 6.  $t_{rr}$  WAVEFORMS AND DEFINITIONS

$I = 1A$   
 $L = 40mH$   
 $R < 0.1\Omega$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$   
 $Q_1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

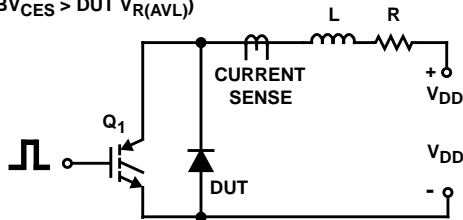


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

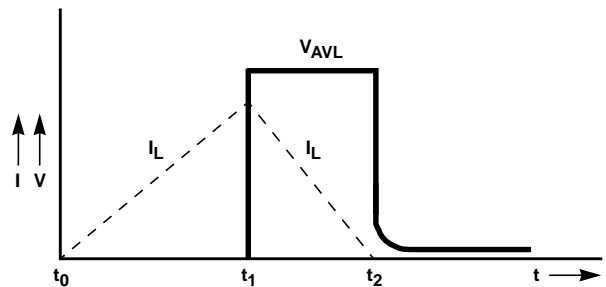


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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